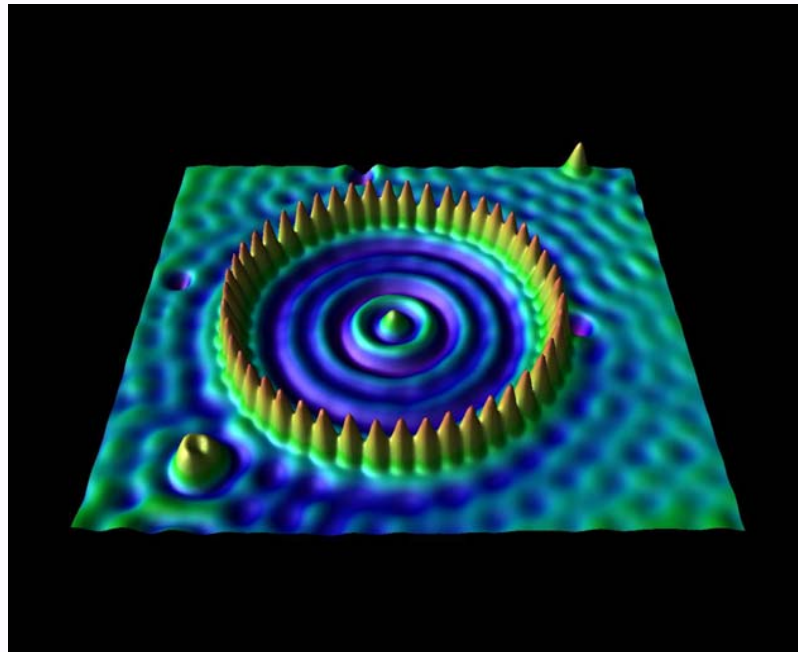


# Lecture 25: Surfaces – Scanning Tunneling Microscope



**Special Presentation Today by Prof. Raffi BUdakian  
On  
Magnetic Resonance Force Microscopy**

Physics 460 F 2006 Lect 25

# Outline

- Surfaces of crystals
- Example – surfaces of semiconductors – GaAs
- **Tunneling in quantum mechanics**  
Particles can tunnel through barriers
- **Scanning tunneling microscope -- STM**
- Examples of GaAs, Mn on GaAs, adatoms on Cu, atoms on GaN surface that illustrate growth, ....
- AFM – very brief

# Surface structure – example: GaAs

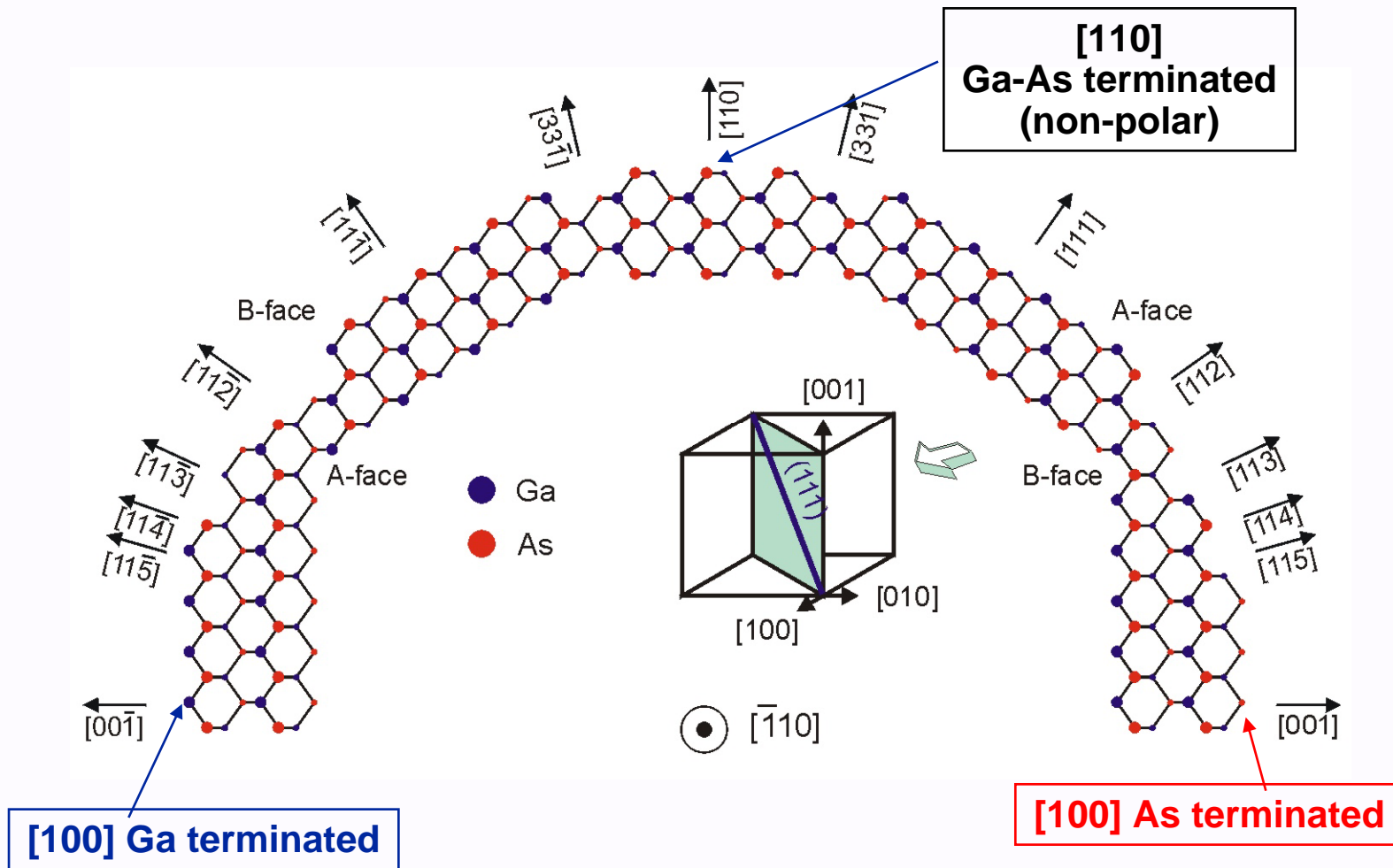


Figure from [w3.rz-berlin.mpg.de/pc/ElecSpec/MBE/mbe.html](http://w3.rz-berlin.mpg.de/pc/ElecSpec/MBE/mbe.html)

# Surface structure – example: GaAs

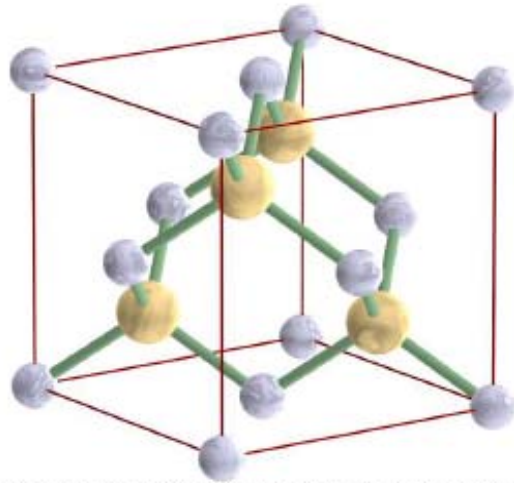
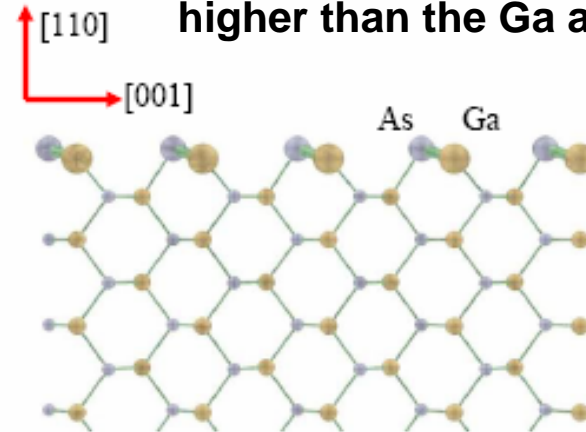


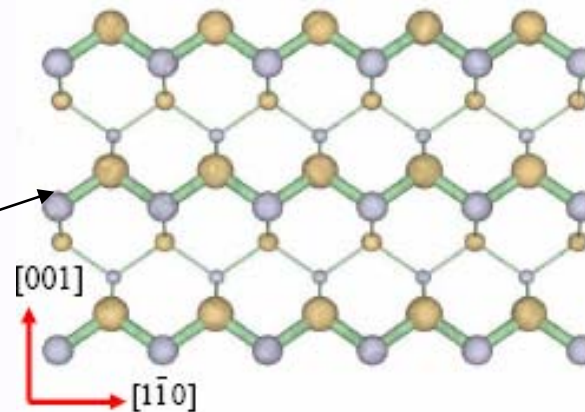
Figure 2.1: The unit cell of GaAs in a Zinc Blende structure

**Conventional Cubic Cell  
in the bulk crystal**

**(110) surface -Ga-As terminated  
Note the As atoms are slightly  
higher than the Ga atoms**



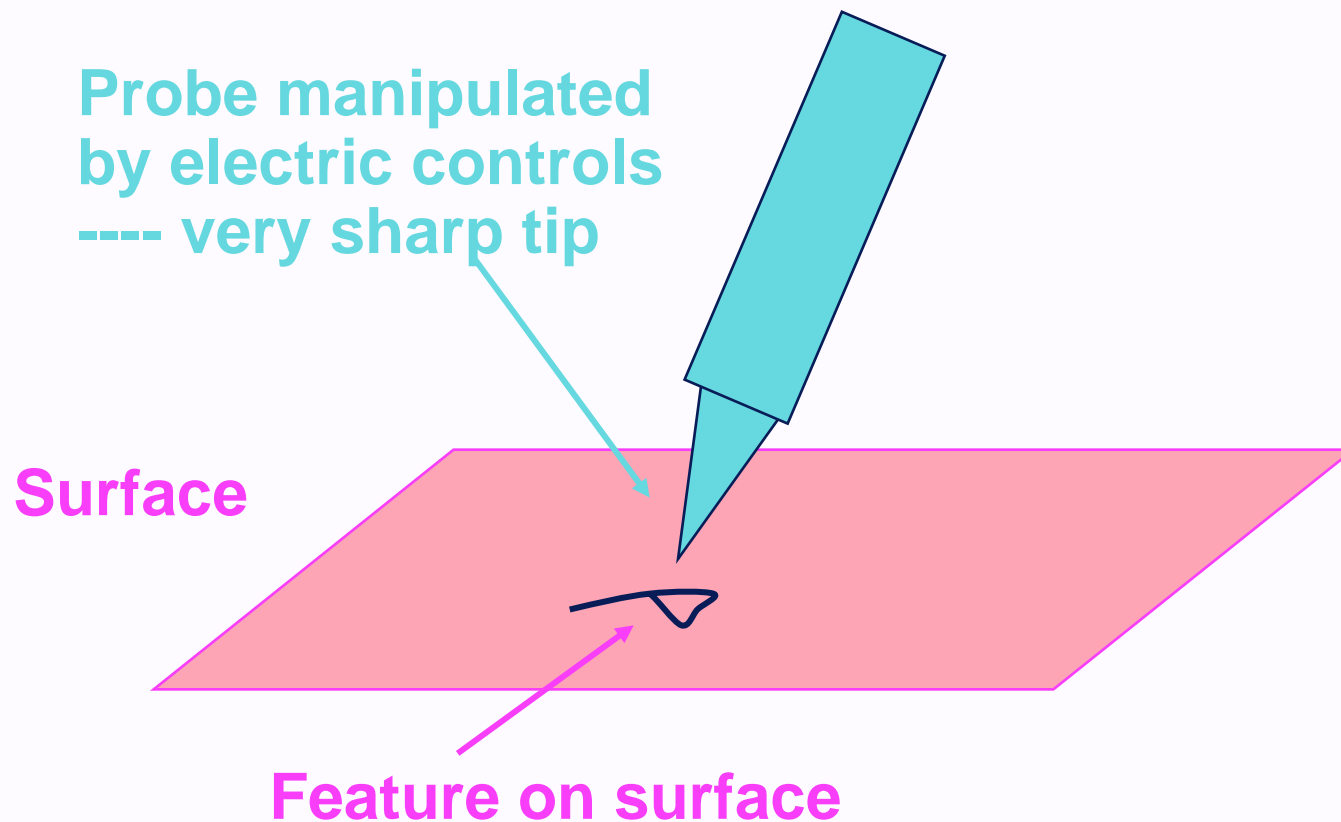
**Top view of (110) surface  
Note zig-zag chains  
of Ga and As atoms**



**Figures from PhD thesis of  
Dale Kitchen, U of Illinois, 2006**

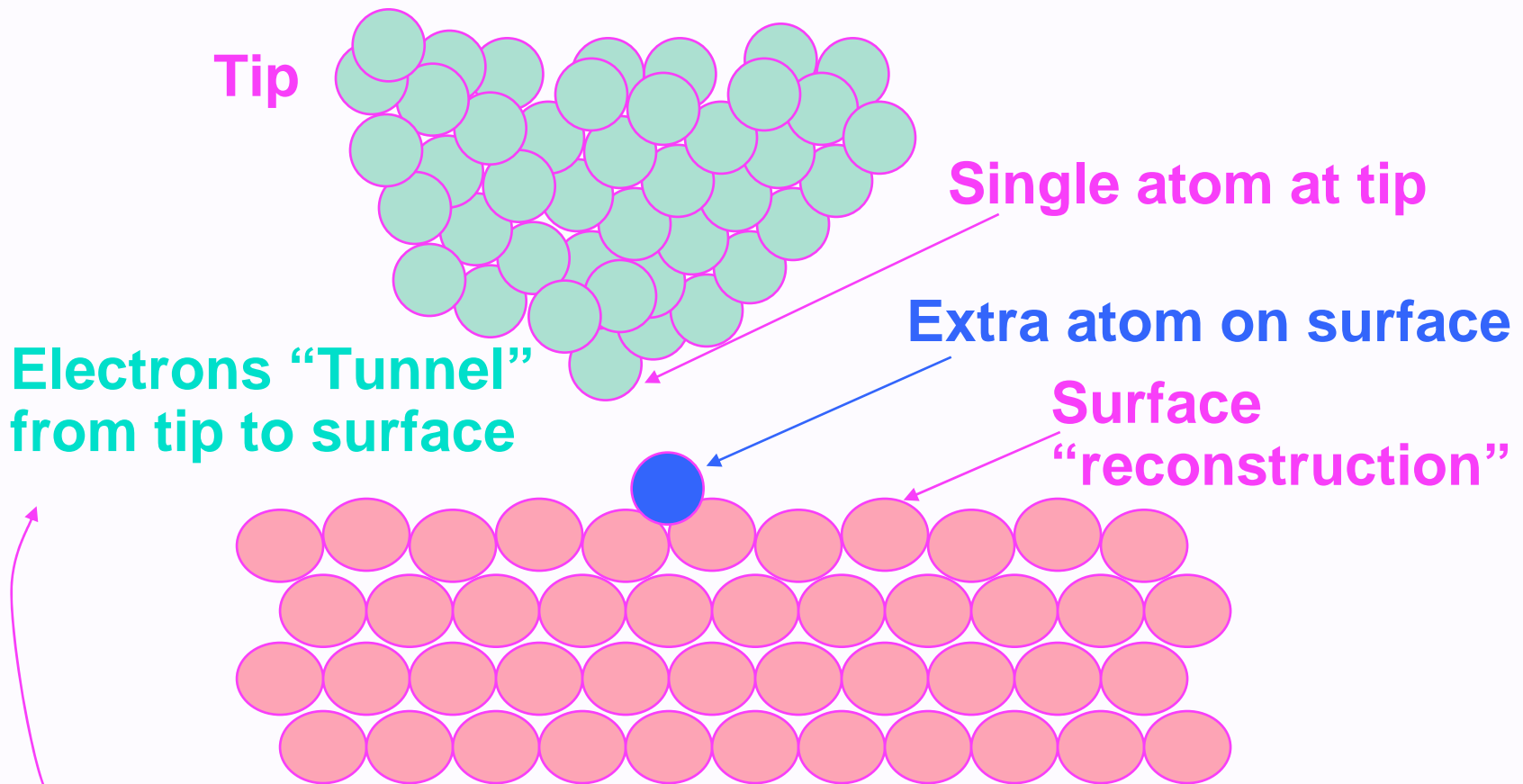
# “Seeing” atomic scale features

“Scanning Tunneling Microscope”  
Measures electric current from tip to surface  
as tip is moved



# Scanning Tunneling Microscope

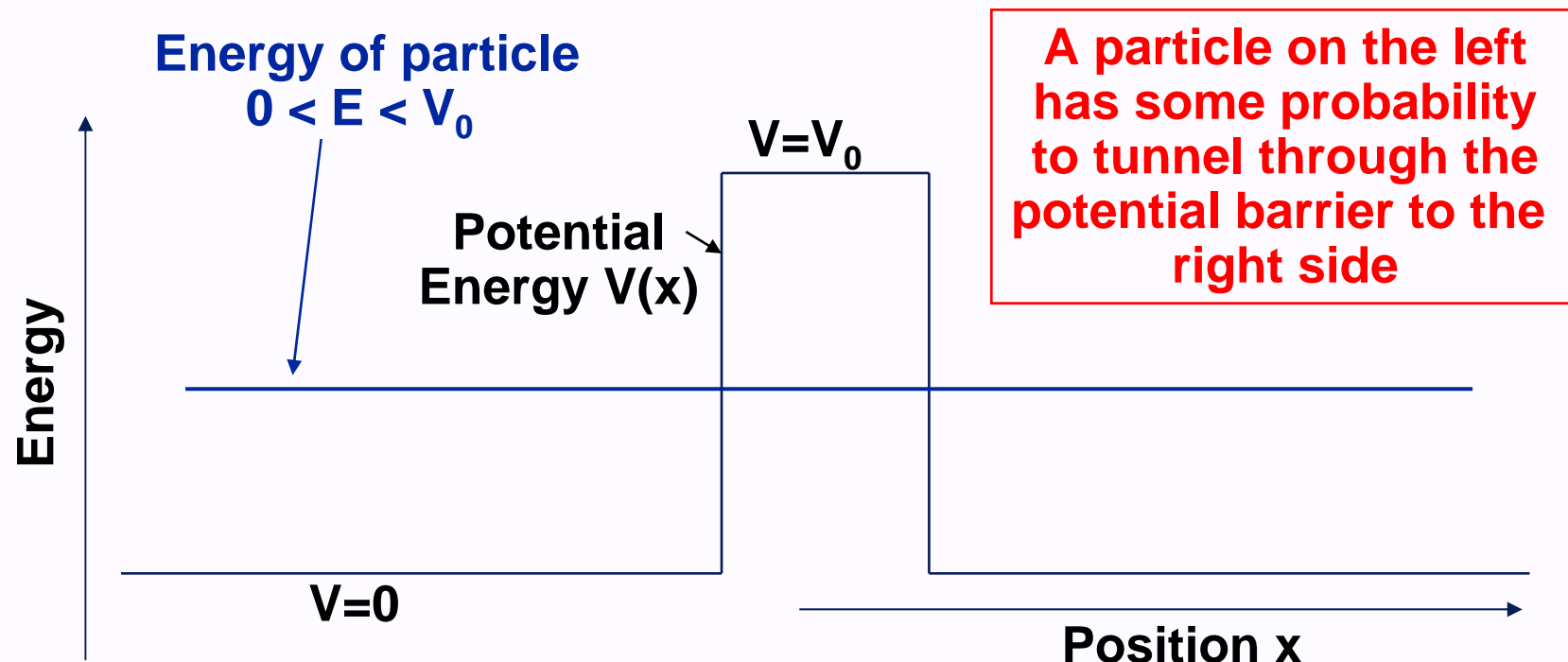
Nobel Prize 1985



Rate of tunneling extremely sensitive to distance of tip from surface due to quantum effects

# “Tunneling” in quantum mechanics

- In Quantum Mechanics has a non-zero probability to be in region that is “classically forbidden”
- A particle can tunnel through a barrier even though it does not have enough energy to get over the barrier



# Schrodinger Equation

- Basic equation of Quantum Mechanics

$$\left[ - (\hbar^2/2m)d^2/dx^2 + V(x) \right] \Psi (x) = E \Psi (x)$$

where we consider only one dimension

$m$  = mass of particle

$V(x)$  = potential energy at point  $x$

$E$  = eigenvalue = energy of quantum state

$\Psi (x)$  = wavefunction

$n (x) = | \Psi (x) |^2$  = probability density

- **Key issue for tunneling:** What happens if the energy  $E$  is less than the potential  $V$  at some point  $x$



# Schrodinger Equation II

- Consider the case where  $V = \text{constant} = V_0$

$$[ - (\hbar^2/2m)(d^2/dx^2) + V_0 ] \Psi (x) = E \Psi (x)$$

which can be written

or  $(\hbar^2/2m) (d^2/dx^2) \Psi (x) = [V_0 - E] \Psi (x)$

$$(d^2/dx^2)\Psi (x) = -k^2 \Psi (x), \quad k^2 = (E - V_0)(2m/\hbar^2)$$

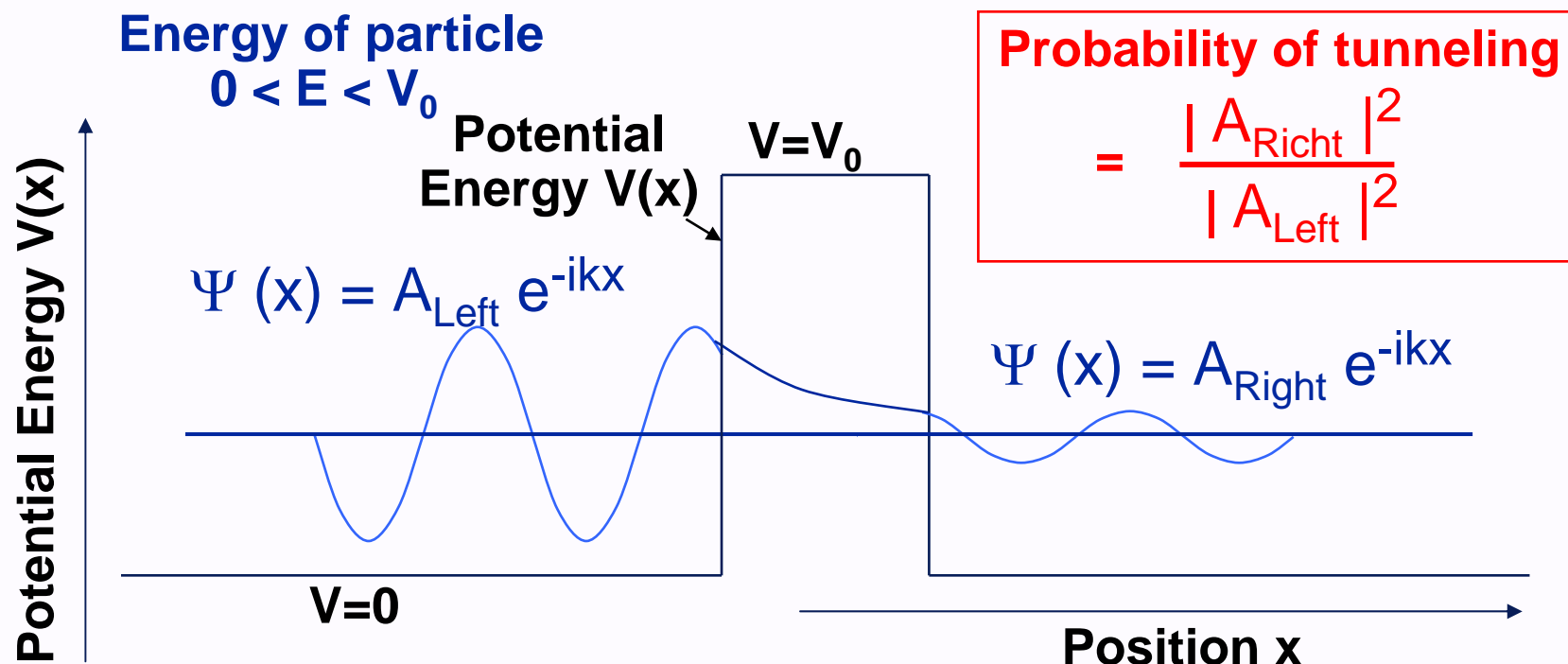
- If  $E > V_0$ ,  $\Psi (x) \sim e^{-ikx}$  (the same as before)

- If  $E < V_0$ , define  $\kappa^2 = -k^2$ ,  
 $\Psi (x) \sim e^{-\kappa x}$

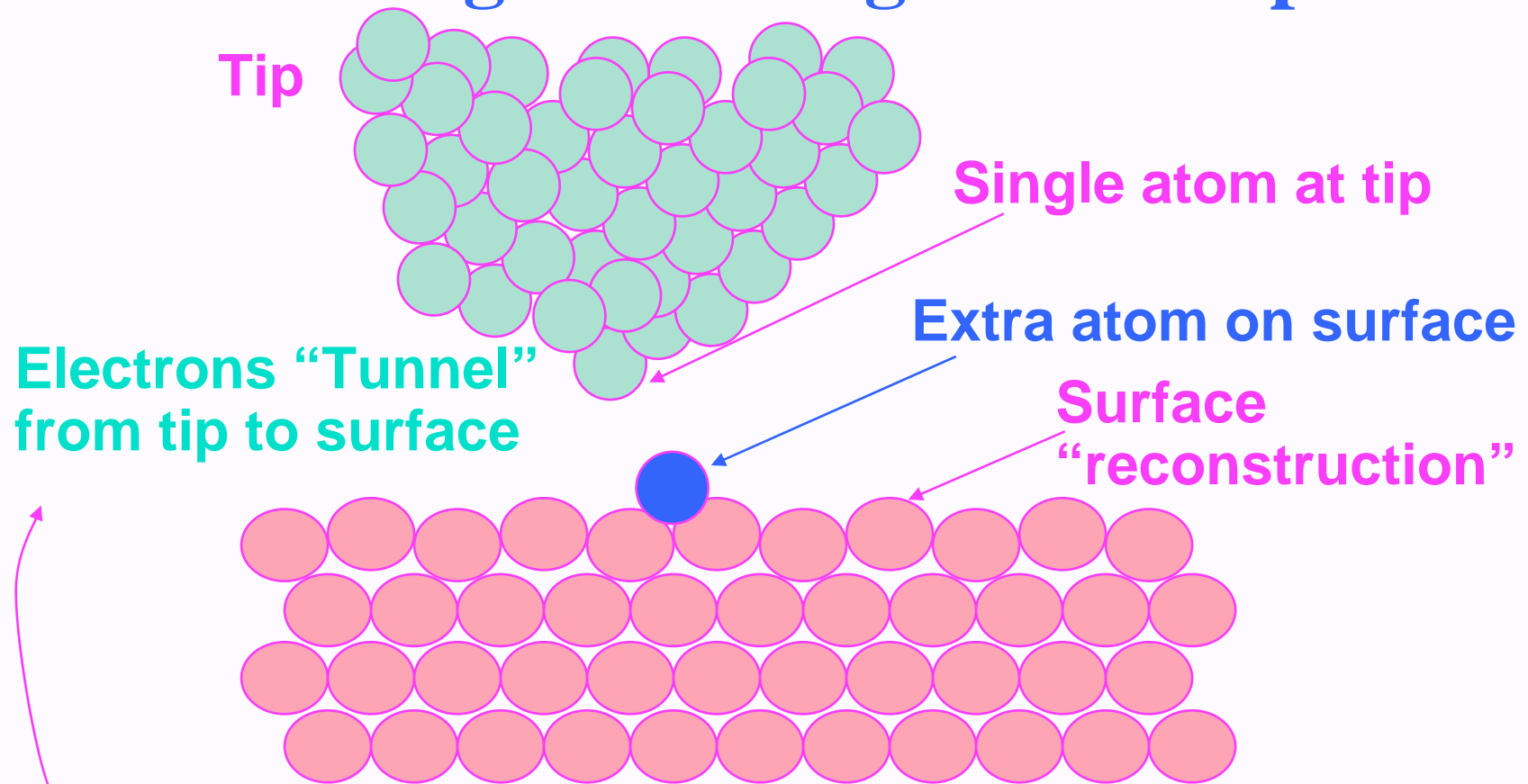
- The wavefunction decays exponentially in the region where  $E < V$

# “Tunneling” in quantum mechanics

- In Quantum Mechanics has a non-zero probability to be in region that is “classically forbidden”
- A particle can tunnel through a barrier even though it does not have enough energy to get over the barrier



# Scanning Tunneling Microscope



Electrons "Tunnel"  
from tip to surface

Single atom at tip

Extra atom on surface

Surface  
"reconstruction"

Probability for an electron to "tunnel" from the metal  
tip to the surface varies rapidly with the distance

# STM images – example: GaAs

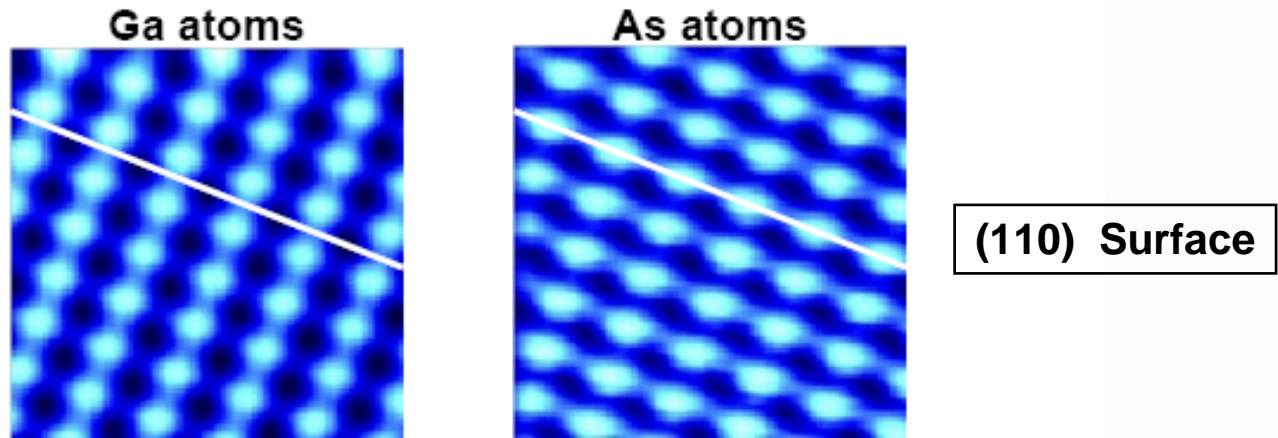
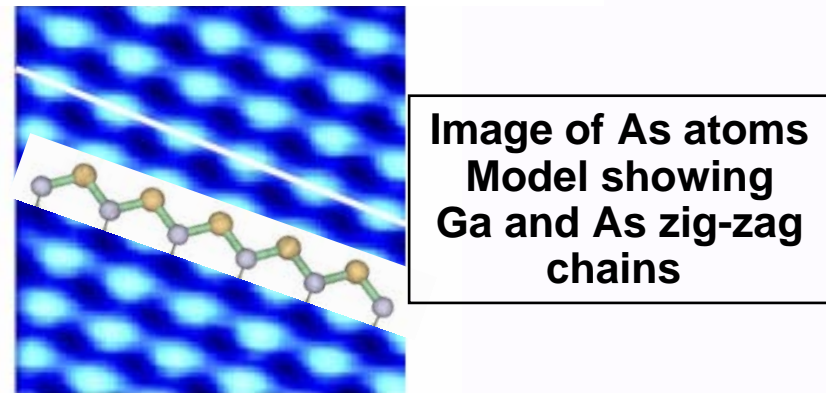
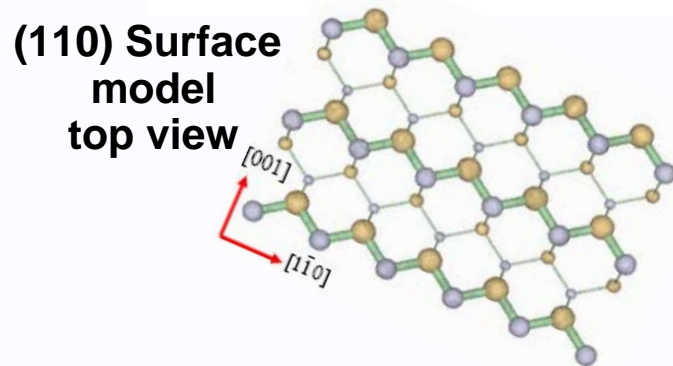


Figure 4.4: The empty states image (left) shows the Ga atoms at +2 V. The filled states image (right) shows the As atoms at -2 V. White lines are to guide eye to identical locations.



# STM image - Mn atom on GaAs

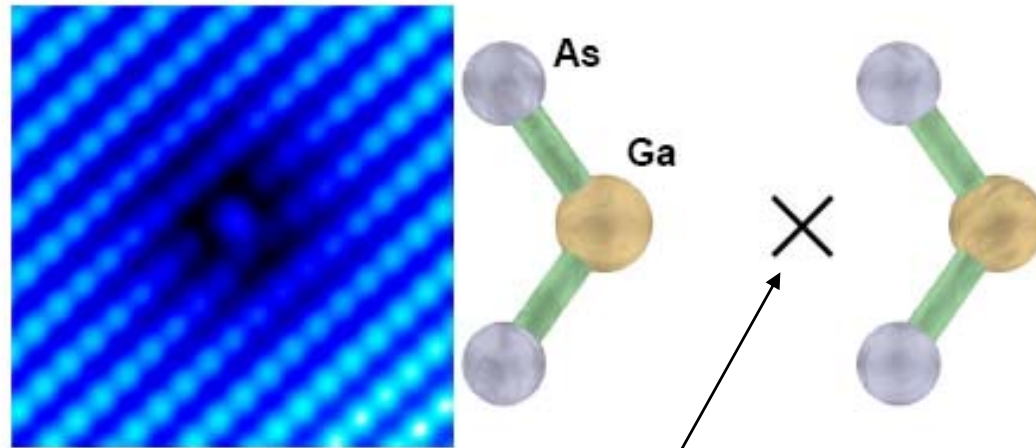


Figure 5.6: A Mn adatom is seen on the As sublattice (Filled states, -1.5 V) in a 50x50 Å area. The Mn adatom is positioned between two of the As rows. The Mn sits between two Ga sites.

**GaAs (110) Surface with one added Mn atom  
at position indicated by x**

# STM image – subsurface atoms

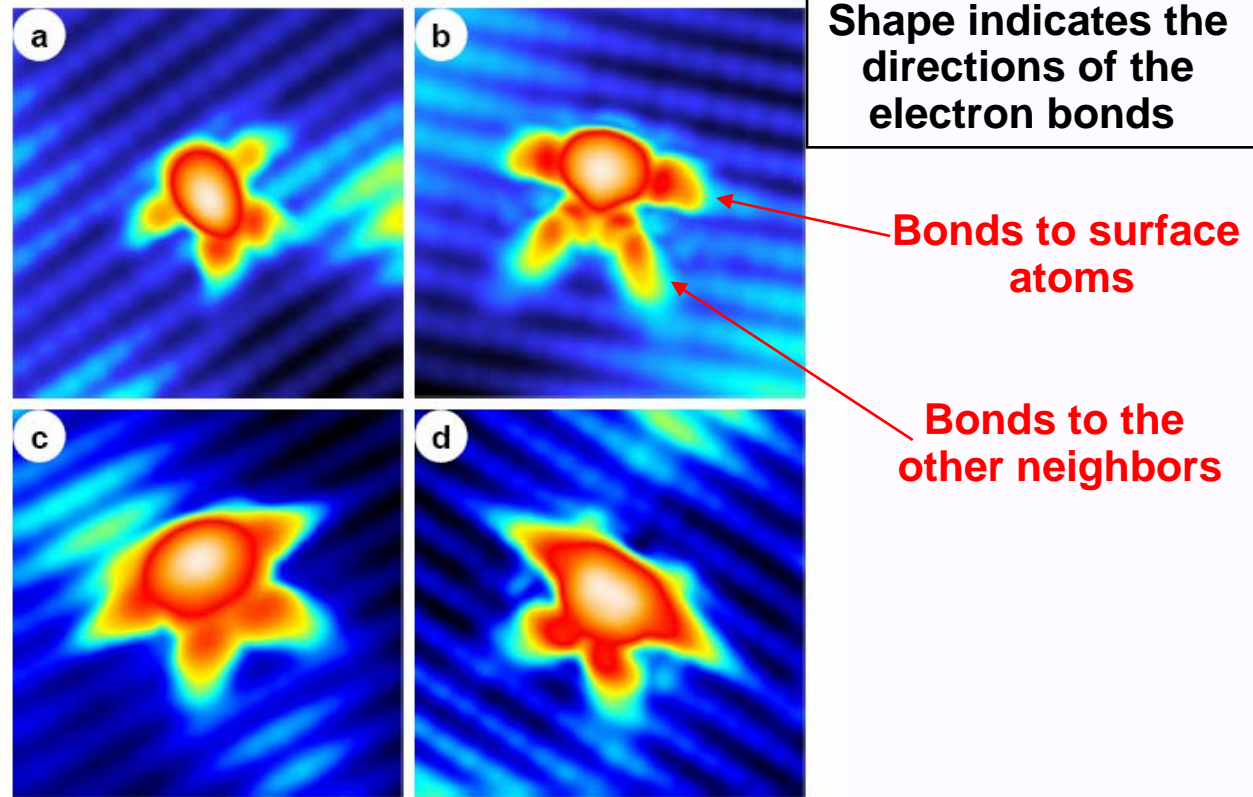
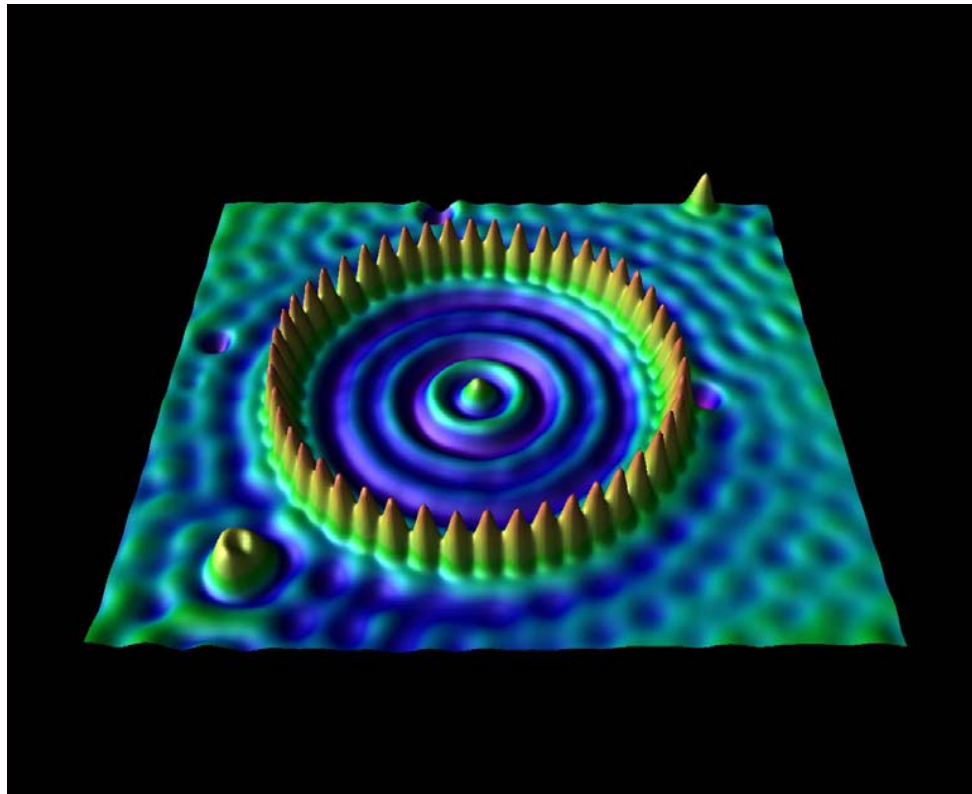


Figure 5.16: Empty states topography (50x50 Å) at conduction band bottom (+1.5 V) captures the in-gap resonances. The isolated impurities are (a) Zn, (b) Mn, (c) Fe, and (d) Co acceptors.

**GaAs (110) surface with Zn, Mn, Fe or Co atoms substituted for Ga in the first layer below the surface**

# Observation of atoms, electron waves with Scanning Tunneling Microscope





# Observation of atoms, electron waves with Scanning Tunneling Microscope

Corral of atoms placed one at the time  
by maneuvering atoms with STM

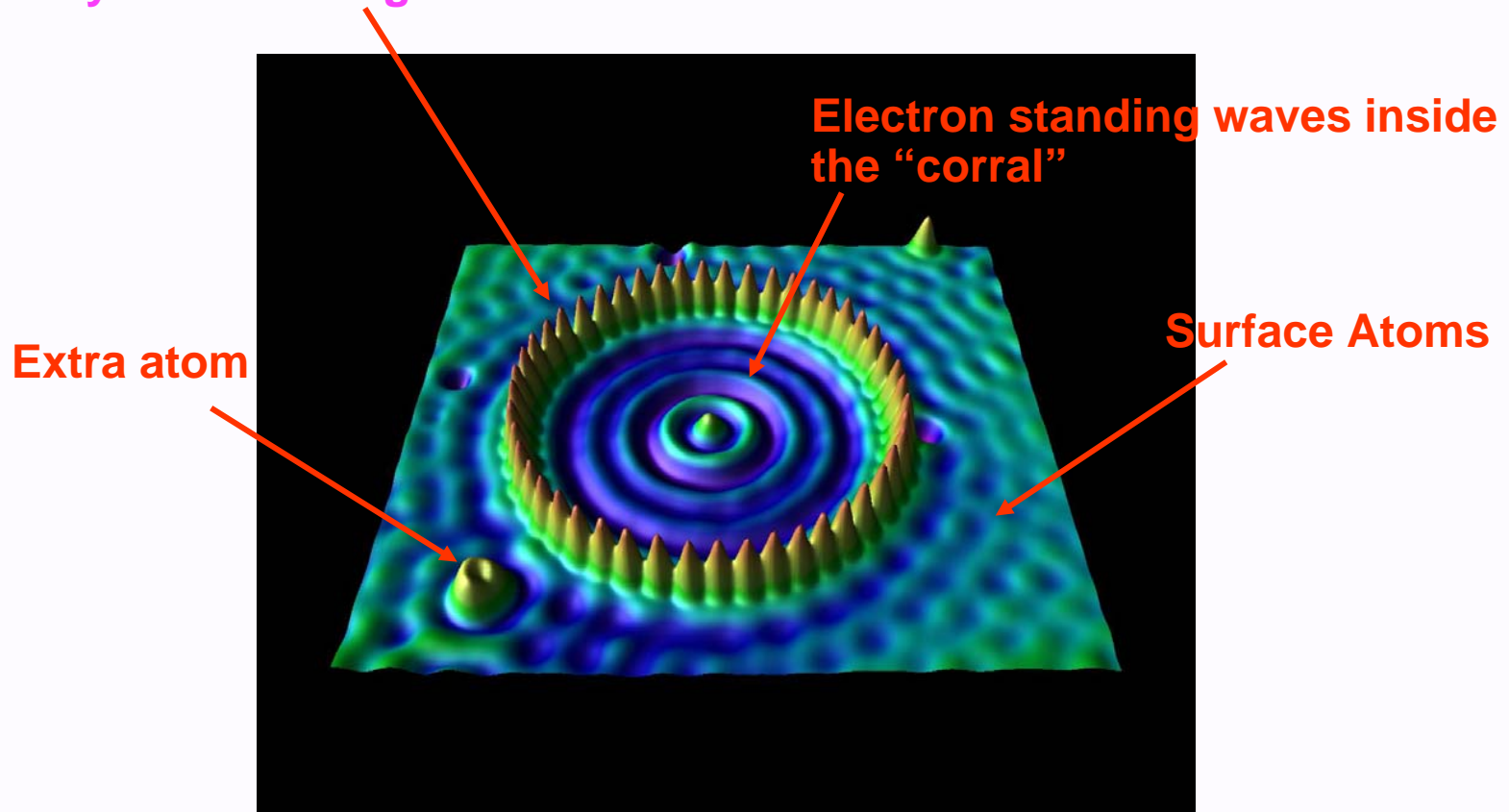


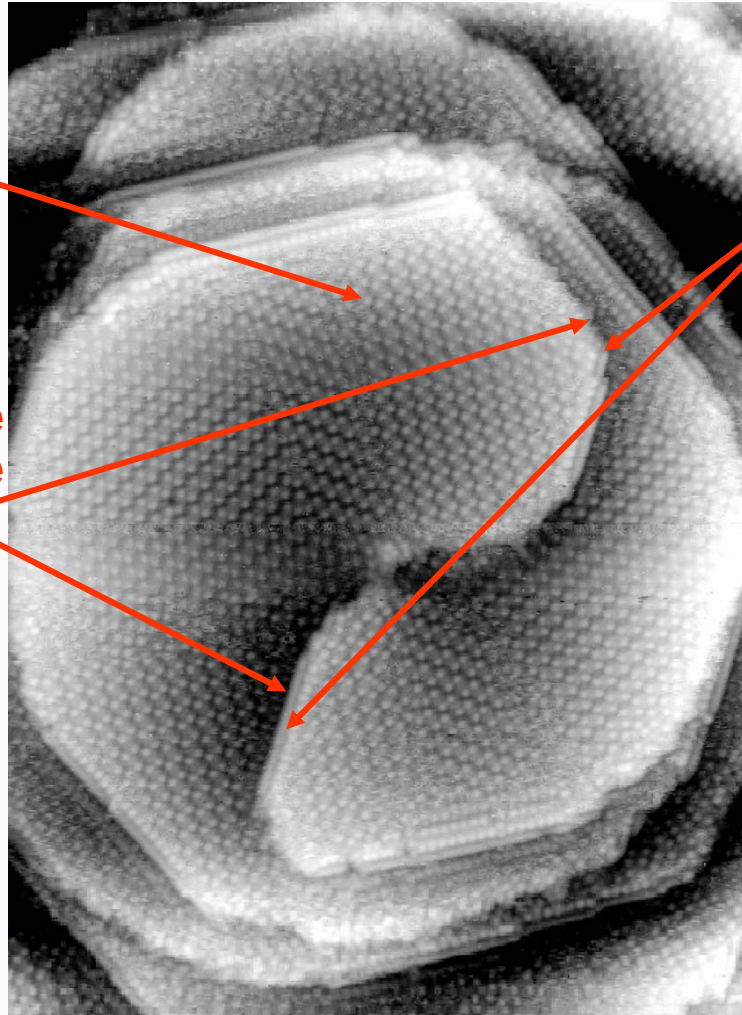
Figure by D. Eigler, et. al, IBM Research



# Surface of GaN observed by STM

Atomic scale structure of surface

“Step” on surface where the surface height changes by one layer



Spiral growth -- A common way that crystals grow -- by adding atoms at a step, the higher layer grows over the lower layer – continues in a spiral

Adding atoms at step makes step move to cover lower layer

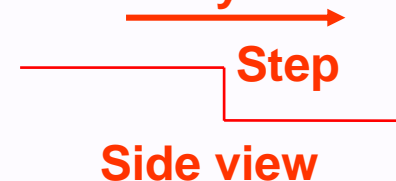
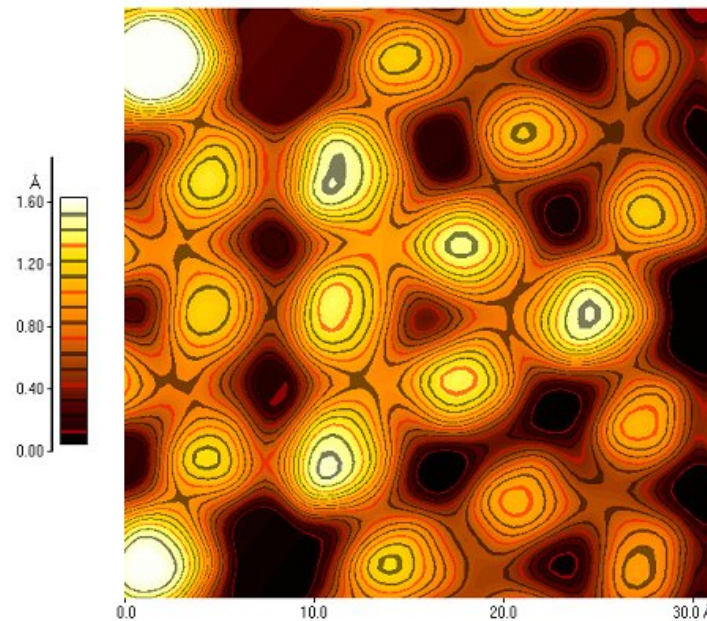
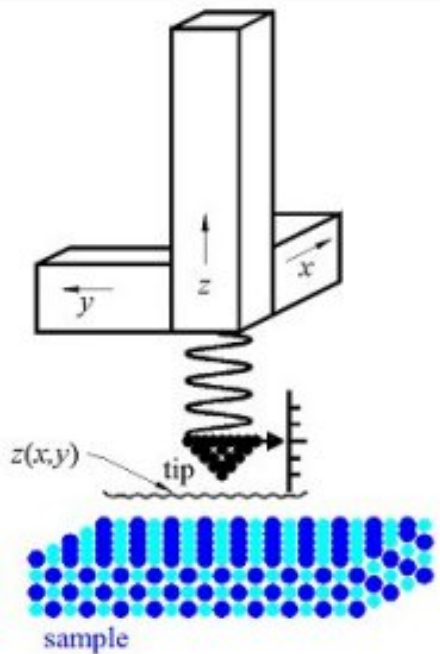


Figure by D. Smith, reproduced in *Electronic Structure*, by R. M. Martin, Cambridge University Press 2004

# Atomic Force Microscope

Article in Physics Today, December, 2006

Works for insulators, ....



Si (111) surface

From [http://www.physik.uni-augsburg.de/exp6/research/sxm/sxm\\_e.shtml](http://www.physik.uni-augsburg.de/exp6/research/sxm/sxm_e.shtml)

# Summary

- Surfaces of crystals
- Example – surfaces of semiconductors – GaAs
- **Tunneling in quantum mechanics**  
Particles can tunnel through barriers  
Exponential decay where  $E < V$
- **STM – electrons tunnel through space between tip and sample**  
Leads to the extreme sensitivity of tunneling current to the distance of tip to sample  
Dominated by a single atom on tip
- Examples of GaAs, Mn on GaAs, adatoms on Cu, atoms on GaN surface that illustrate growth, ....
- AFM – very brief

# Next Lecture

- **Nanostructures**

**Magnetic, superconducting**

- **Final lecture ---- Summary of course**